

**Amendments to the Claims:**

The following claims will replace all prior versions of the claims in this application (in the unlikely event that no claims follow herein, the previously pending claims will remain):

1-11. (Cancelled)

12. (Previously Presented) A method for manufacturing a nano-gap electrode device, comprising:

forming a first electrode on a substrate;

forming a separation layer with a predetermined thickness all over the substrate including the first electrode;

removing a portion or all of the separation layer on the first electrode;

forming a second electrode on the separation layer, which is formed on the substrate at a side of the first electrode; and

forming a nano-gap between the first electrode and the second electrode, by completely removing the separation layer remained therebetween.

13. (Original) The method as claimed in claim 12, wherein the separation layer is formed with the same thickness as a width of the nano-gap, and deposited with the same thickness on a surface and a sidewall of the first electrode, and the substrate.

14. (Original) The method as claimed in claim 12, wherein the separation layer is formed with a material having high etching selectivity to the substrate and the first electrode.

15. (Original) The method as claimed in claim 12, wherein the second electrode is formed with a thickness thinner than that of the first electrode.

16. (Previously Presented) The method as claimed in claim 12, wherein the electrode material is not deposited on the sidewall of the separation layer at the time of a deposition process for forming the second electrode.